

SEP 03 2002

REQUEST FOR CONTINUED EXAMINATION (RCE) TRANSMITTAL

Address to:
Commissioner for Patents
Box RCE
Washington, DC 20231

Application Number	09/414,226
Filing Date	October 7, 1999
First Named Inventor	Chang, C-P
Art Unit	2811 #12/RCE
Examiner Name	Donghee Kang 9/17/02
Attorney Docket Number	Chang 7-20-10

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This is a Request for Continued Examination (RCE) under 37 CFR 1.114 of the above-identified application. Request for Continued Examination (RCE) practice under 37 CFR 1.114 does not apply to any utility or plant application filed prior to June 8, 1995, or to any design application. See Instruction Sheet for RCEs (not to be submitted to the USPTO) on page 2.

1. Submission required under 37 CFR 1.114

- a. ☐ Previously submitted
- i. ☐ Consider the amendment(s)/reply under 37 CFR 1.116 previously filed on _____
(Any unentered amendment(s) referred to above will be entered).
- ii. ☐ Consider the arguments in the Appeal Brief or Reply Brief previously filed on _____
- iii. ☐ Other _____
- b. ☒ Enclosed
- i. ☒ Amendment/Reply
- ii. ☐ Affidavit(s)/Declaration(s)
- iii. ☐ Information Disclosure Statement (IDS)
- iv. ☐ Other _____

2. Miscellaneous

- a. ☐ Suspension of action on the above-identified application is requested under 37 CFR 1.103(c) for a period of _____ months. (Period of suspension shall not exceed 3 months; Fee under 37 CFR 1.17(i) required)
- b. ☐ Other _____

3. Fees The RCE fee under 37 CFR 1.17(e) is required by 37 CFR 1.114 when the RCE is filed.

- a. ☒ The Director is hereby authorized to charge the following fees, or credit any overpayments, to Deposit Account No. 50-1735
- i. ☒ RCE fee required under 37 CFR 1.17(e) (\$740.00)
- ii. ☐ Extension of time fee (37 CFR 1.136 and 1.17) 09/05/2002 SSESHE1 00000060 501735 99414226
- iii. ☐ Other 01 FC:179 740.00 CH
- b. ☐ Check in the amount of \$ _____ enclosed
- c. ☐ Payment by credit card (Form PTO-2038 enclosed)

WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038.

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT REQUIRED

Name (Print /Type)	Richard J. Botos	Registration No. (Attorney/Agent)	32,016
Signature	<i>Richard J. Botos</i>	Date	August 26, 2002

CERTIFICATE OF MAILING OR TRANSMISSION

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner For Patents, Box RCE, Washington, DC 20231, or facsimile transmitted to the U.S. Patent and Trademark Office on the date shown below.

Name (Print/Type)	Judith A. WilliamsMatthew	Date	August 26, 2002
Signature	<i>J. WilliamsMatthew</i>		

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U.S. Serial No. 09/414,226
Chang 7-20-10

IN THE UNITED STATES
PATENT AND TRADEMARK OFFICE

Patent Application

Inventor(s): Chorng-Ping Chang
Chien-Shing Pai
Thi-Hong-Ha Vuong

Case: 7-20-10

Serial No.: 09/414,226

Group Art Unit: 2811

Filing Date: October 7, 1999

Examiner: Donghee Kang

Title: Semiconductor Device with Tapered Gate and Process For
Fabricating the Device

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

REQUEST FOR CONTINUING EXAMINATION

This Request for Continued Examination is in response to the FINAL
Office Action mailed August 22, 2002.

IN THE CLAIMS

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1. (twice amended) A semiconductor device comprising:
- a semiconductor substrate in which a source, drain and channel are
formed;
- a gate formed on a gate dielectric layer formed on the semiconductor
substrate;
- spacers adjacent to the gate wherein the gate is interposed between the
spacers and the gate and spacers are formed in a trench formed in a layer of

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9/17/02
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